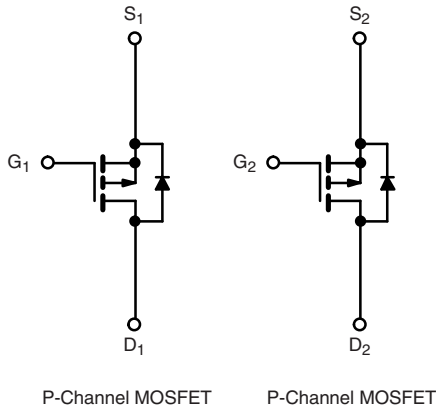


## Dual P-Channel 20-V (D-S) MOSFET

### PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ )   | $I_D$ (A) <sup>d</sup> | $Q_g$ (Typ.) |
|--------------|-----------------------------|------------------------|--------------|
| - 20         | 0.013 at $V_{GS} = - 4.5$ V | -7.5                   | 20 nC        |
|              | 0.018 at $V_{GS} = - 2.5$ V | -6.5                   |              |
|              | 0.032 at $V_{GS} = - 1.8$ V | -5.0                   |              |



### FEATURES

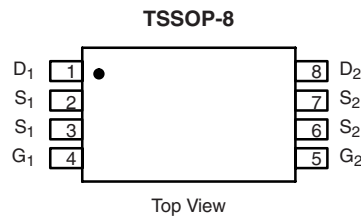
- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 %  $R_g$  Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Adaptor Switch
- High Current Load Switch
- Notebook



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

| Parameter  | Symbol         | Limit                 | Unit |
|--|----------------|-----------------------|------|
| Drain-Source Voltage                             | $V_{DS}$       | - 20                  | V    |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 12$              |      |
| Continuous Drain Current ( $T_J = 150$ °C)       | $T_C = 25$ °C  | - 7.5                 | A    |
|  | $T_C = 70$ °C  | - 6.0                 |      |
|  | $T_A = 25$ °C  | - 5.4 <sup>a, b</sup> |      |
|  | $T_A = 70$ °C  | - 4.5 <sup>a, b</sup> |      |
| Pulsed Drain Current                             | $I_{DM}$       | - 30                  |      |
| Continuous Source-Drain Diode Current            | $T_C = 25$ °C  | - 4.1                 |      |
|  | $T_A = 25$ °C  | - 2.1 <sup>a, b</sup> |      |
| Avalanche Current                                | $I_{AS}$       | - 15                  | mJ   |
| Single-Pulse Avalanche Energy                    | $E_{AS}$       | 11.25                 |      |
| Maximum Power Dissipation                        | $T_C = 25$ °C  | 5                     | W    |
|  | $T_C = 70$ °C  | 3.2                   |      |
|  | $T_A = 25$ °C  | 2.5 <sup>a, b</sup>   |      |
|  | $T_A = 70$ °C  | 1.6 <sup>a, b</sup>   |      |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$ | - 55 to 150           | °C   |

### THERMAL RESISTANCE RATINGS

| Parameter                                   | Symbol     | Typical | Maximum | Unit |
|---|------------|---------|---------|------|
| Maximum Junction-to-Ambient <sup>a, c</sup> | $R_{thJA}$ | 38      | 50      | °C/W |
| Maximum Junction-to-Foot                    | $R_{thJF}$ | 20      | 25      |      |

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b.  $t = 10$  s.

c. Maximum under steady state conditions is 85 °C/W.

d. Based on  $T_C = 25$  °C.

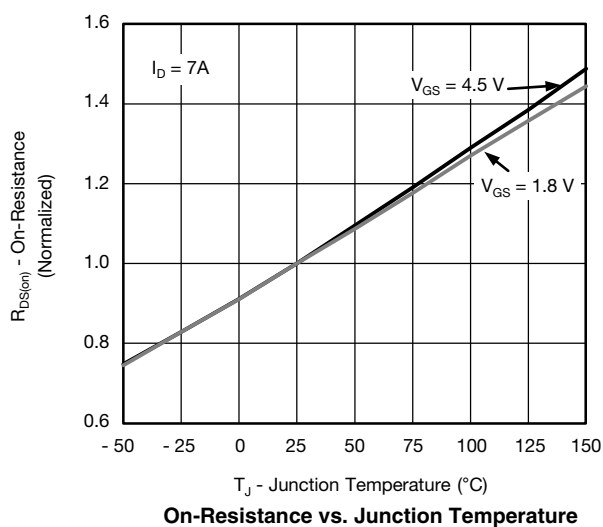
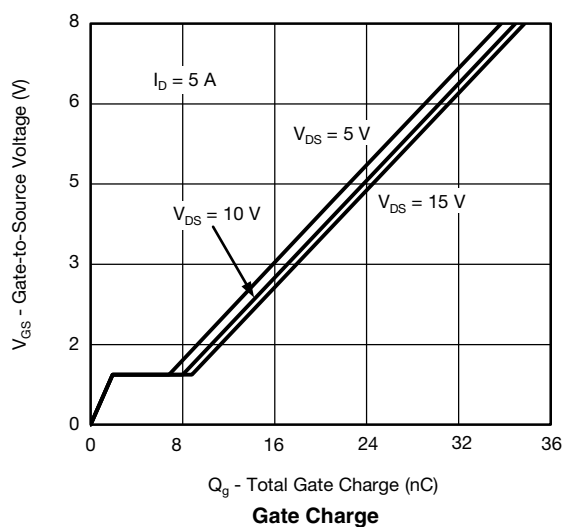
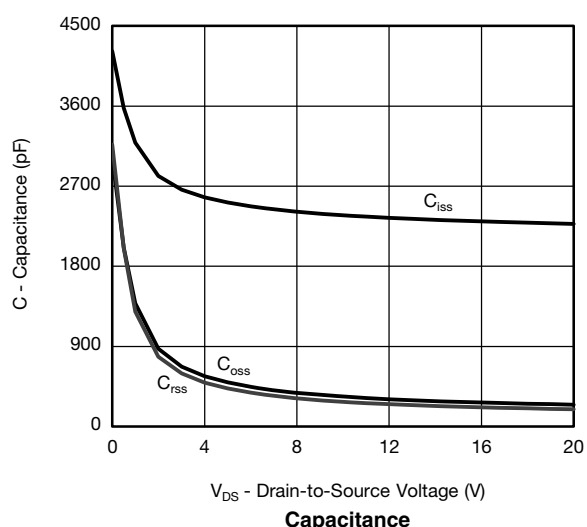
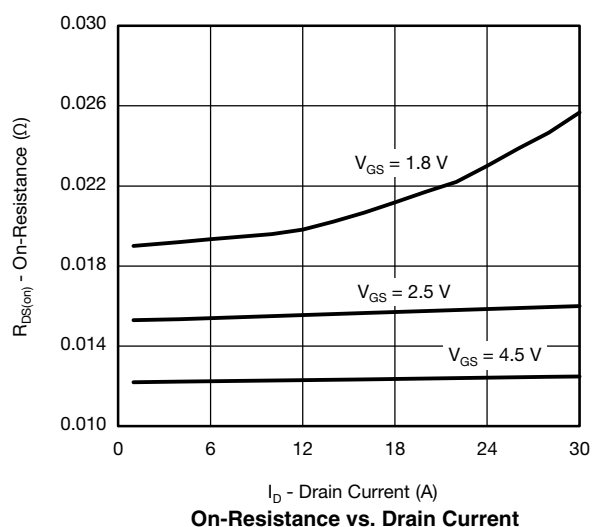
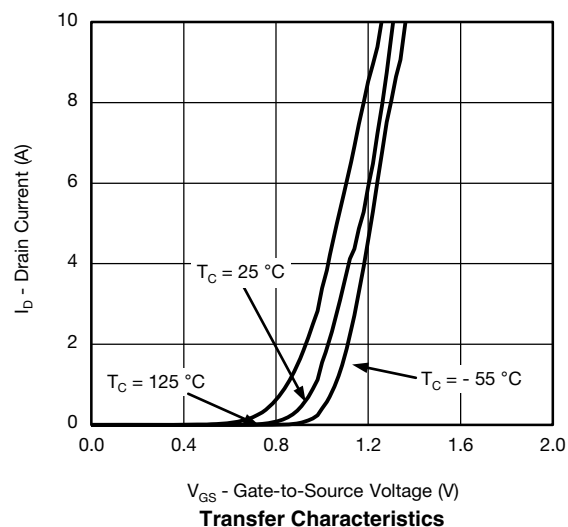
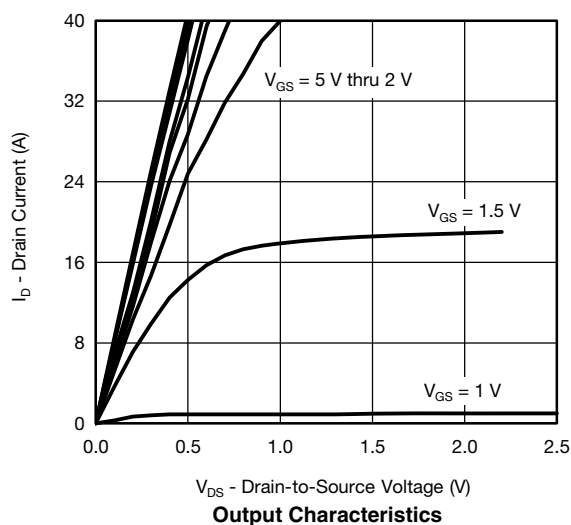
| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                                      |  |       |        |       |       |
|---|--------------------------------------|--|-------|--------|-------|-------|
| Parameter   | Symbol                               | Test Conditions  | Min.  | Typ.   | Max.  | Unit  |
| Static  |                                      |  |       |        |       |       |
| Drain-Source Breakdown Voltage                                  | V <sub>DS</sub>                      | V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA   | - 20  |        |       | V     |
| V <sub>DS</sub> Temperature Coefficient                         | ΔV <sub>DS</sub> /T <sub>J</sub>     | I <sub>D</sub> = - 250 μA  |       | - 14.5 |       | mV/°C |
| V <sub>GS(th)</sub> Temperature Coefficient                     | ΔV <sub>GS(th)</sub> /T <sub>J</sub> |  |       | 2.8    |       |       |
| Gate-Source Threshold Voltage                                   | V <sub>GS(th)</sub>                  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA  | - 0.4 |        | - 1.0 | V     |
| Gate-Source Leakage   | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V   |       |        | ± 100 | nA    |
| Zero Gate Voltage Drain Current                                 | I <sub>DSS</sub>                     | V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V  |       |        | - 1   | μA    |
|   |                                      | V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C  |       |        | - 10  |       |
| On-State Drain Current <sup>a</sup>                             | I <sub>D(on)</sub>                   | V <sub>DS</sub> ≥ - 10 V, V <sub>GS</sub> = - 5 V  | - 20  |        |       | A     |
| Drain-Source On-State Resistance <sup>a</sup>                   | R <sub>DS(on)</sub>                  | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 7 A  |       | 0.013  |       | Ω     |
|   |                                      | V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 6 A  |       | 0.018  |       |       |
|   |                                      | V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 3 A  |       | 0.032  |       |       |
| Forward Transconductance <sup>a</sup>                           | g <sub>fs</sub>                      | V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 9 A   |       | 40     |       | S     |
| Dynamic <sup>b</sup>  |                                      |  |       |        |       |       |
| Input Capacitance   | C <sub>iss</sub>                     | V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz   |       | 2380   |       | pF    |
| Output Capacitance  | C <sub>oss</sub>                     |  |       | 340    |       |       |
| Reverse Transfer Capacitance                                    | C <sub>rss</sub>                     |  |       | 280    |       |       |
| Total Gate Charge   | Q <sub>g</sub>                       | V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 8 V, I <sub>D</sub> = - 5 A  |       | 45     | 70    | nC    |
| Gate-Source Charge  | Q <sub>gs</sub>                      | V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A  |       | 20     | 35    |       |
| Gate-Drain Charge   | Q <sub>gd</sub>                      |  |       | 3.1    |       |       |
| Gate Resistance   | R <sub>g</sub>                       |  |       | 8.4    |       |       |
| Gate Resistance   | R <sub>g</sub>                       | f = 1 MHz  | 1.0   | 4.8    | 9.6   | Ω     |
| Turn-On Delay Time  | t <sub>d(on)</sub>                   | V <sub>DD</sub> = - 10 V, R <sub>L</sub> = 2 Ω<br>I <sub>D</sub> ≅ - 5 A, V <sub>GEN</sub> = - 8 V, R <sub>g</sub> = 1 Ω   |       | 7      | 14    | ns    |
| Rise Time   | t <sub>r</sub>                       |  |       | 9      | 18    |       |
| Turn-Off DelayTime  | t <sub>d(off)</sub>                  |  |       | 108    | 200   |       |
| Fall Time   | t <sub>f</sub>                       |  |       | 41     | 80    |       |
| Turn-On Delay Time  | t <sub>d(on)</sub>                   | V <sub>DD</sub> = - 10 V, R <sub>L</sub> = 2 Ω<br>I <sub>D</sub> ≅ - 5 A, V <sub>GEN</sub> = - 4.5 V, R <sub>g</sub> = 1 Ω |       | 14     | 28    |       |
| Rise Time   | t <sub>r</sub>                       |  |       | 16     | 32    |       |
| Turn-Off DelayTime  | t <sub>d(off)</sub>                  |  |       | 101    | 200   |       |
| Fall Time   | t <sub>f</sub>                       |  |       | 40     | 80    |       |
| Drain-Source Body Diode Characteristics                         |                                      |  |       |        |       |       |
| Continous Source-Drain Diode Current                            | I <sub>S</sub>                       | T <sub>C</sub> = 25 °C   |       |        | - 4.1 | A     |
| Pulse Diode Forward Current                                     | I <sub>SM</sub>                      |  |       |        | - 40  |       |
| Body Diode Voltage  | V <sub>SD</sub>                      | I <sub>S</sub> = - 3 A, V <sub>GS</sub> = 0 V  |       | - 0.66 | - 1.2 | V     |
| Body Diode Reverse Recovery Time                                | t <sub>rr</sub>                      | I <sub>F</sub> = - 2.3 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C   |       | 81     | 150   | ns    |
| Body Diode Reverse Recovery Charge                              | Q <sub>rr</sub>                      |  |       | 150    | 300   | nC    |
| Reverse Recovery Fall Time                                      | t <sub>a</sub>                       |  |       | 43     |       | ns    |
| Reverse Recovery Rise Time                                      | t <sub>b</sub>                       |  |       | 38     |       |       |

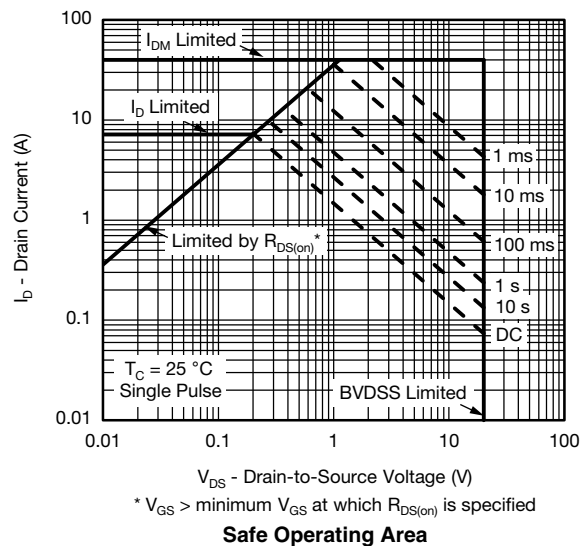
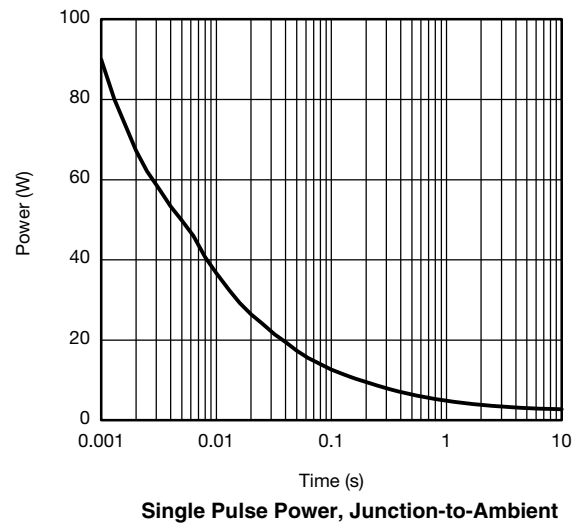
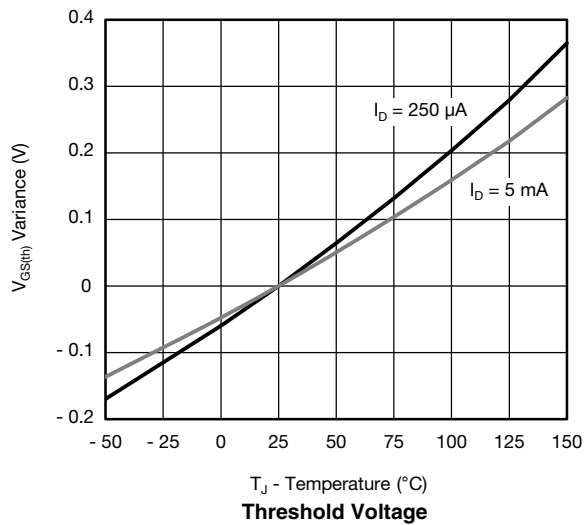
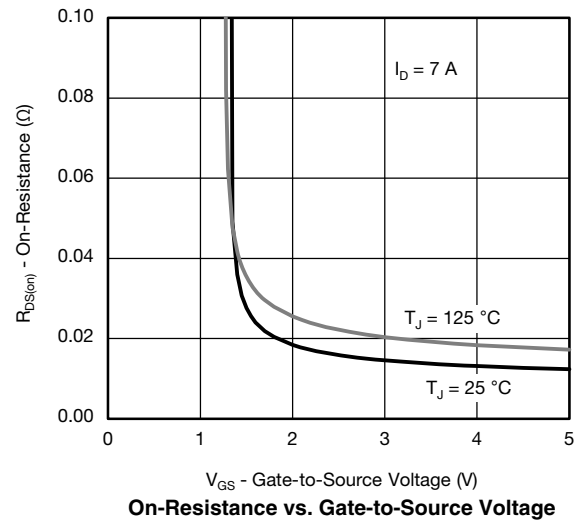
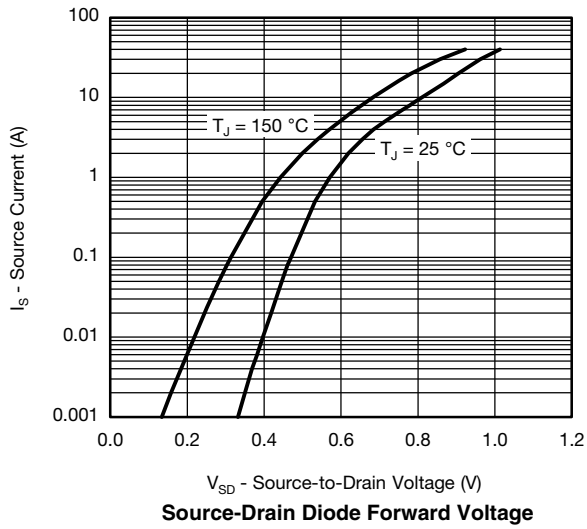
Notes:

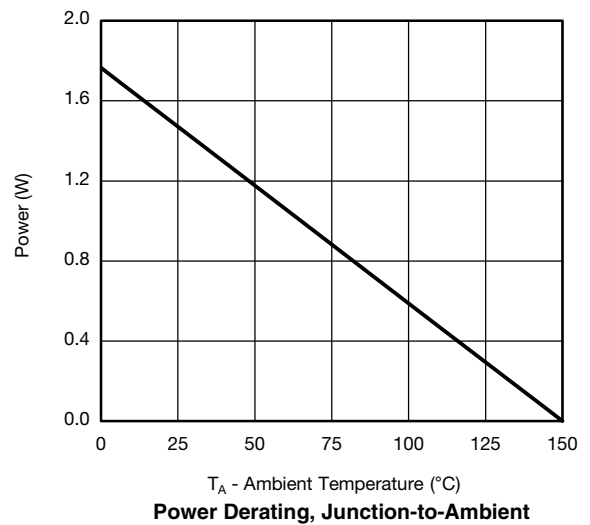
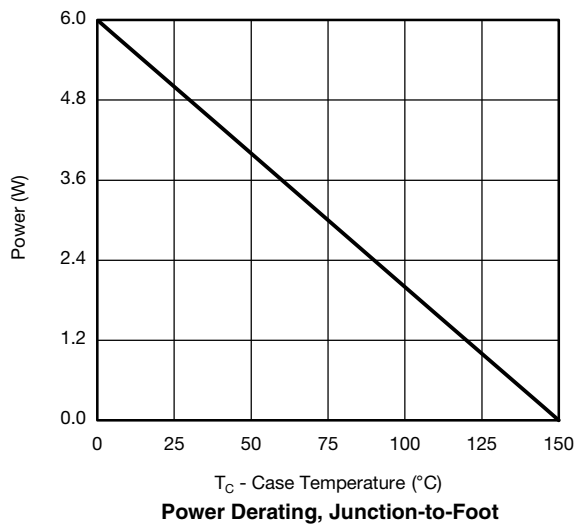
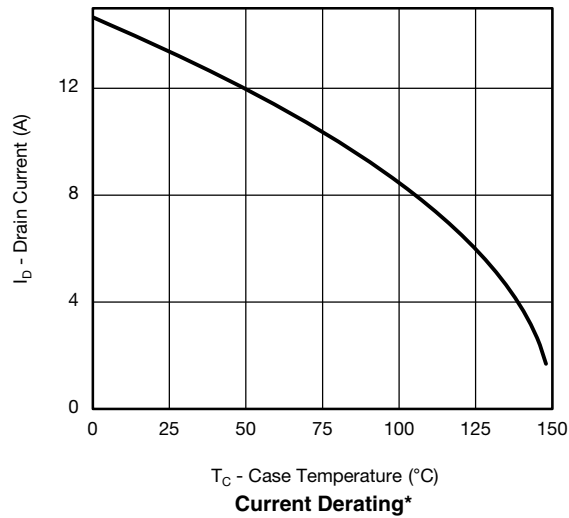
a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

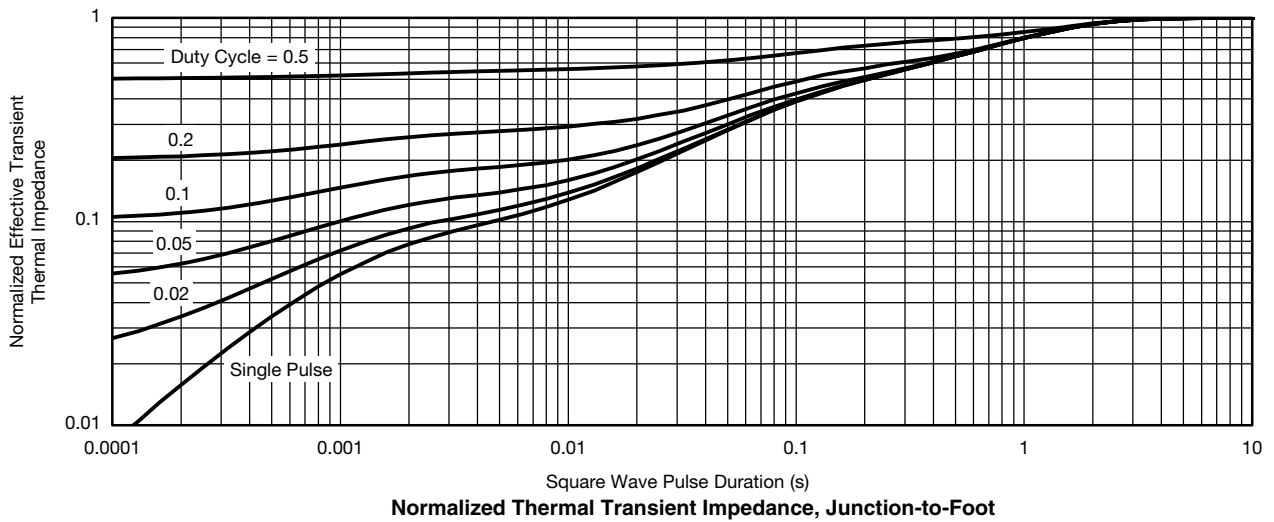
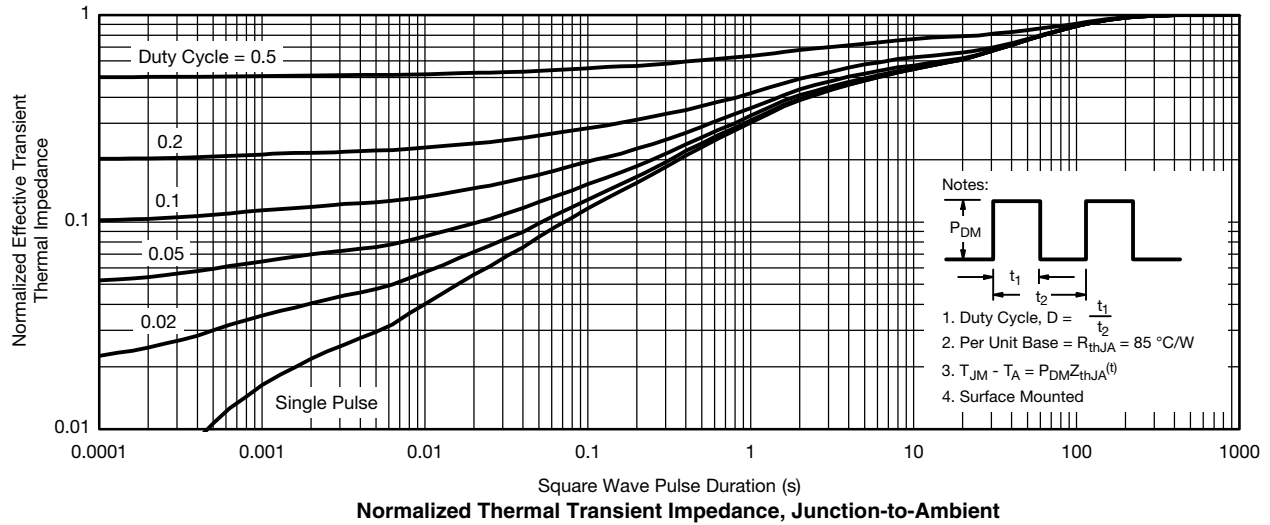
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


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\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



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